

**Micro Commercial Components** 



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## MCG16P03

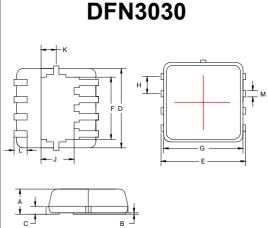
# **Features**

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Halogen free available upon request by adding suffix "-HF"
- Epoxy meets UL 94 V-0 flammability rating
- Moisture Sensitivity Level 1

## Maximum Ratings @ 25°C Unless Otherwise Specified

Symbol	Parameter	Rating	Unit	
$V_{DS}$	Drain-source Voltage	-30	V	
I <sub>D</sub>	Drain Current-Continuous T <sub>C</sub> = 25°C	-16	Α	
	$T_{C} = 100^{\circ}C$	-12	Α	
I <sub>DM</sub>	Pulsed Drain Current (Note 1)	- 80	Α	
$V_{GS}$	Gate-source Voltage	±20	V	
$P_D$	Maximum Power Dissipation	35	W	
$R_{thJC}$	Thermal Resistance, Junction-to-Case(Note 2)	3.57	°C/W	
E <sub>AS</sub>	Single pulse avalanche energy (Note 5)	90	mj	
$T_J$	Operating Junction Temperature	-55 to +150	$^{\circ}\!\mathbb{C}$	
T <sub>STG</sub>	Storage Temperature	-55 to +150	$^{\circ}\! \mathbb{C}$	

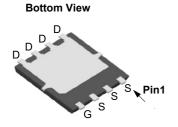
# P-Channel Power MOSFET

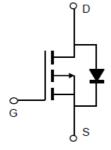


c d	В	

DIM	INCHES		INCHES MM		INCHES MM		
	MIN	MAX	MIN	MAX	NOTE		
Α	0.028	0.035	0.70	0.90			
В	0.000	0.002	0.00	0.05			
С	0.004	0.010	0.10	0.25			
D	0.118 BSC		3.0	0 BSC			
E	0.126 BSC		3.2	0 BSC			
F	0.093 BSC		2.3	5 BSC			
G	0.118 BSC		3.0	0 BSC			
Н	0.026 BSC		0.6	5 BSC			
J	0.069 BSC		1.7	5 BSC			
K	0.023BSC		0.5	75 BSC			
L	0.012	0.020	0.30	0.50			
М	0.009	0.014	0.24	0.35	1		

#### **EQUIVALENT CIRCUIT**







## **Electrical Characteristics (T<sub>A</sub>=25** ℃ unless otherwise noted)

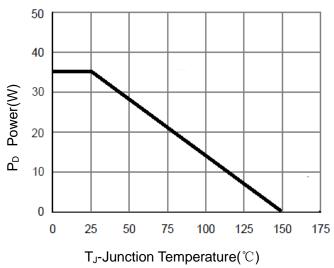
Parameter	Symbol	Condition	Mi n	Тур	Max	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =-250μA	-30	-33	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V,V <sub>GS</sub> =0V	-	-	-1	μΑ
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics (Note 3)	•					
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =-250µA	-1	-1.5	-1.9	V
Prein Course On Otata Basistana	_	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A	-	10.6	15	mΩ
Drain-Source On-State Resistance	KDS(ON)	R <sub>DS(ON)</sub> V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-15A	-	16.3	25	mΩ
Forward Transconductance	<b>g</b> FS	V <sub>DS</sub> =-5V,I <sub>D</sub> =-15A	15	-	-	S
Dynamic Characteristics (Note4)	·					
Input Capacitance	C <sub>Iss</sub>	\/ 25\/\\ 0\/	-	2130	-	PF
Output Capacitance	Coss	$V_{DS}$ =-25V, $V_{GS}$ =0V, F=1.0MHz	-	302	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0WIHZ	-	227	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t <sub>d(on)</sub>		-	12	-	nS
Turn-on Rise Time	t <sub>r</sub>	V <sub>DD</sub> =-15V, ID=-15A,	-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{GS}$ =-10 $V$ , $R_{GEN}$ =1 $\Omega$	-	25	-	nS
Turn-Off Fall Time	tf		-	13	-	nS
Total Gate Charge	Qg		-	45.6	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V,I <sub>D</sub> =-20A,V <sub>GS</sub> =-10V	-	4.6	-	nC
Gate-Drain Charge	$Q_{gd}$		-	11.1	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =-30A	-	-	-1.2	V

#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- **3.** Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition: Tj=25  $^{\circ}\text{C}$  ,VDD=-15V,VG=-4.5V,L=0.5mH,Rg=25  $\Omega$



## **Typical Electrical and Thermal Characteristics**



**Figure 1 Power Dissipation** 

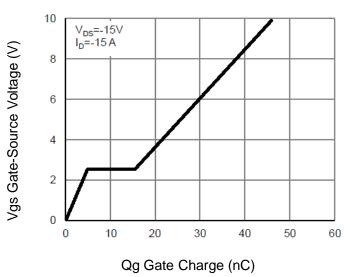
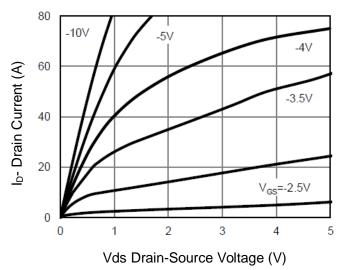


Figure 2 Gate Charge



**Figure 3 Output Characteristics** 

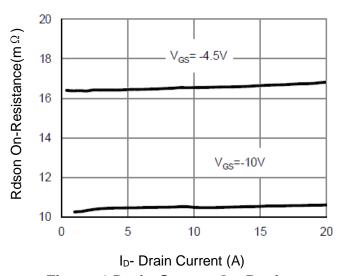
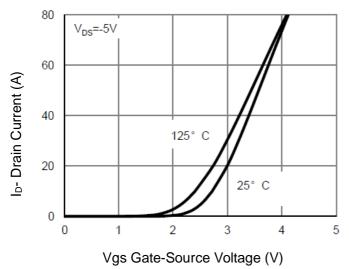


Figure 4 Drain-Source On-Resistance



## **Typical Electrical and Thermal Characteristics**



**Figure 5 Transfer Characteristics** 

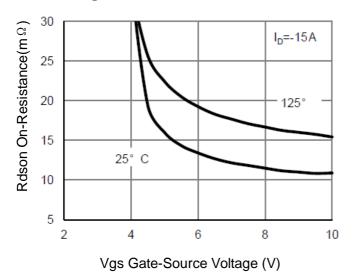


Figure 7 Rdson vs Vgs

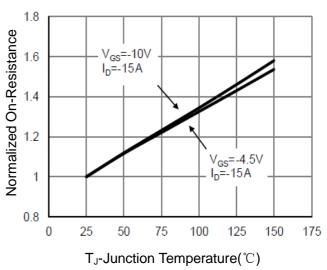


Figure 6 Drain-Source On-Resistance

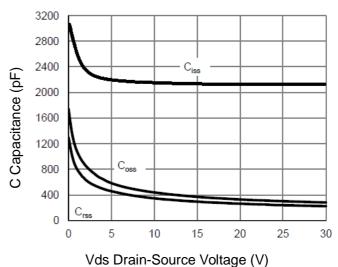


Figure 8 Capacitance vs Vds



### **Ordering Information:**

Device	Packing
Part Number-TP	Tape&Reel:3Kpcs/Reel

Note: Adding "-HF" suffix for halogen free, eg. Part Number-TP-HF

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